

HY1904D/U/V

Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings (Tc=25°C Unless Otherwise Noted)			
V _{DSS}	Drain-Source Voltage	40	V
V _{GSS}	Gate-Source Voltage	±20	V
T _J	Maximum Junction Temperature	175	°C
T _{STG}	Storage Temperature Range	-55 to 175	°C
I _S	Source Current-Continuous(Body Diode)	Tc=25°C 72	A
Mounted on Large Heat Sink			
I _{DM}	Pulsed Drain Current *	Tc=25°C 288	A
I _D	Continuous Drain Current	Tc=25°C 72	A
		Tc=100°C 51	A
P _D	Maximum Power Dissipation	Tc=25°C 62.5	W
		Tc=100°C 31	W
R _{θJC}	Thermal Resistance, Junction-to-Case	2.4	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient **	110	°C/W
E _{AS}	Single Pulsed-Avalanche Energy ***	L=0.3mH 134	mJ

Electrical Characteristics (Cont.) (Tc =25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	HY1904			Unit
			Min	Typ.	Max	
Dynamic Characteristics						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1 MHz	-	1.6	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =25V, Frequency=1.0MHz	-	2164	-	pF
C _{oss}	Output Capacitance		-	202	-	
C _{rss}	Reverse Transfer Capacitance		-	75	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =20V, R _G =4 Ω, I _{DS} =36A, V _{GS} =10V	-	23	-	ns
T _r	Turn-on Rise Time		-	28	-	
t _{d(OFF)}	Turn-off Delay Time		-	29	-	
T _f	Turn-off Fall Time		-	34	-	
Gate Charge Characteristics						
Q _g	Total Gate Charge	V _{DS} =32V, V _{GS} =10V, I _D =36A	-	51.5	-	nC
Q _{gs}	Gate-Source Charge		-	5.5	-	
Q _{gd}	Gate-Drain Charge		-	11	-	

Note: *Pulse test pulse width 300us duty cycle 2%

Typical Operating Characteristics

Figure 1: Power Dissipation

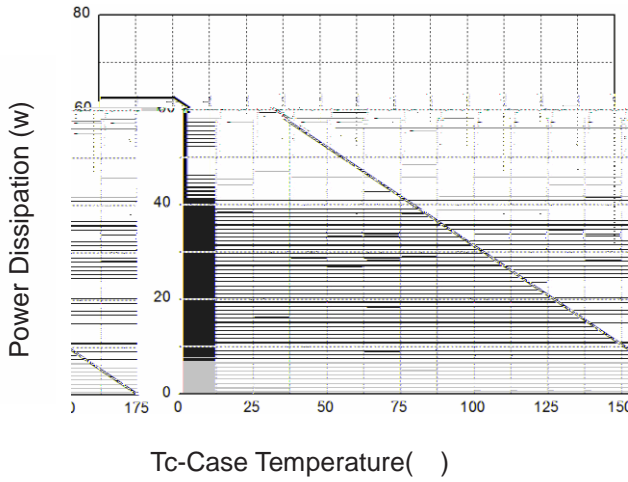


Figure 2: Drain Current

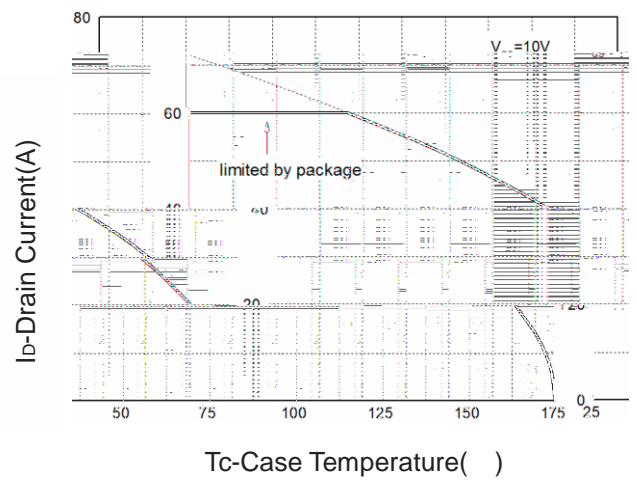


Figure 3: Safe Operation Area

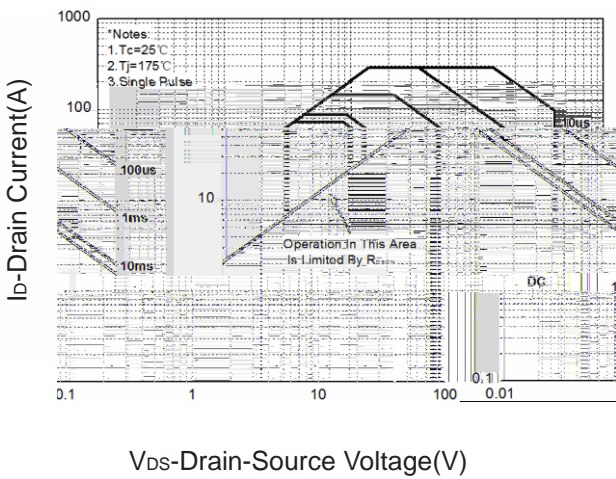


Figure 4: Thermal Transient Impedance

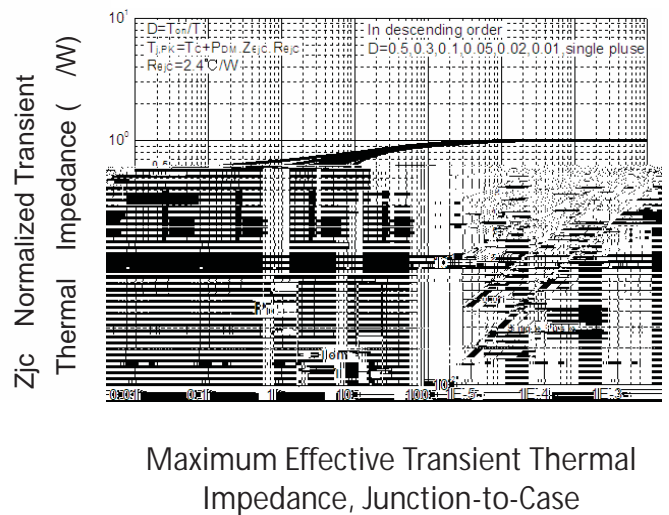


Figure 5: Output Characteristics

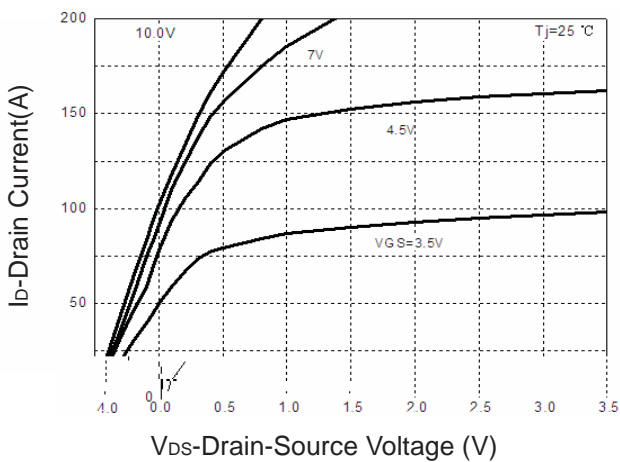
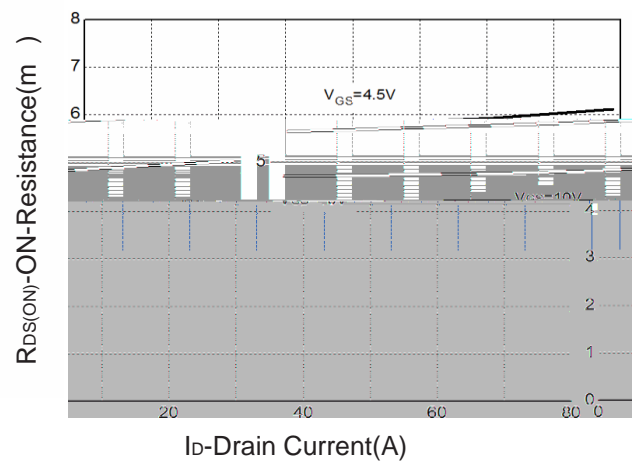


Figure 6: Drain-Source On Resistance



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Typical Operating Characteristics(Cont.)

Figure 7: On-Resistance vs. Temperature

Figure 8: Source-Drain Diode Forward

T_j-Junction Temperature ()

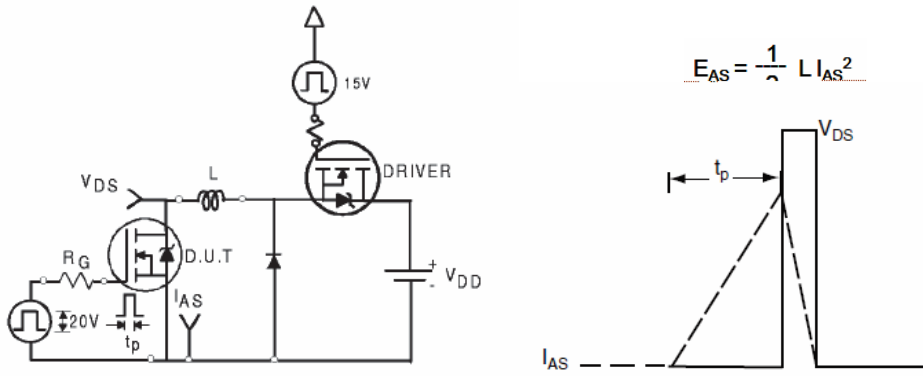
V_{SD}-Source-Drain Voltage(V)

Figure 9: Capacitance Characteristics

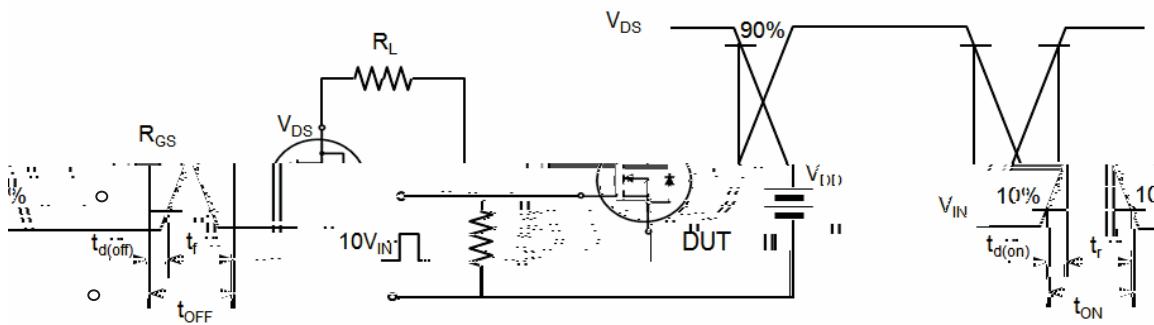
Figure 10: Gate Charge Characteristics

V

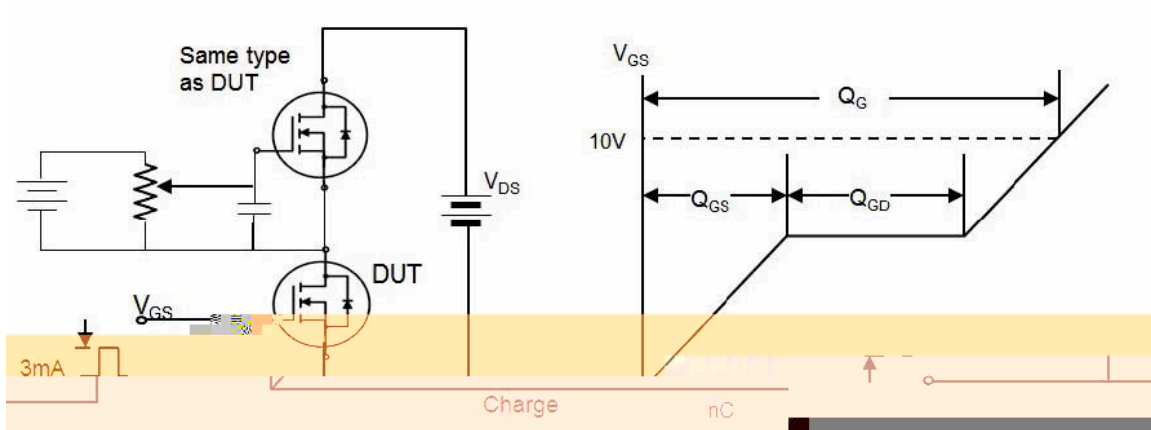
Avalanche Test Circuit



Switching Time Test Circuit



Gate Charge Test Circuit



Device Per Unit

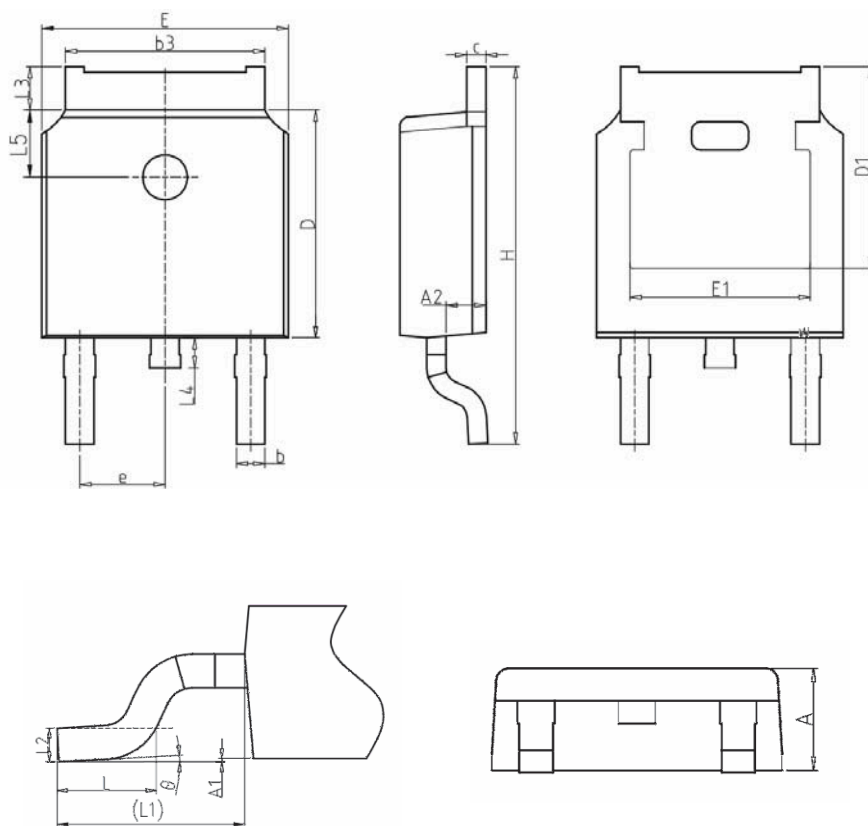
Package Type	Unit	Quantity
TO-252-2L	Tube	75
TO-252-2L	Reel	2500
TO-251-3L	Tube	75
TO-251-3S	Tube	75

Package Information

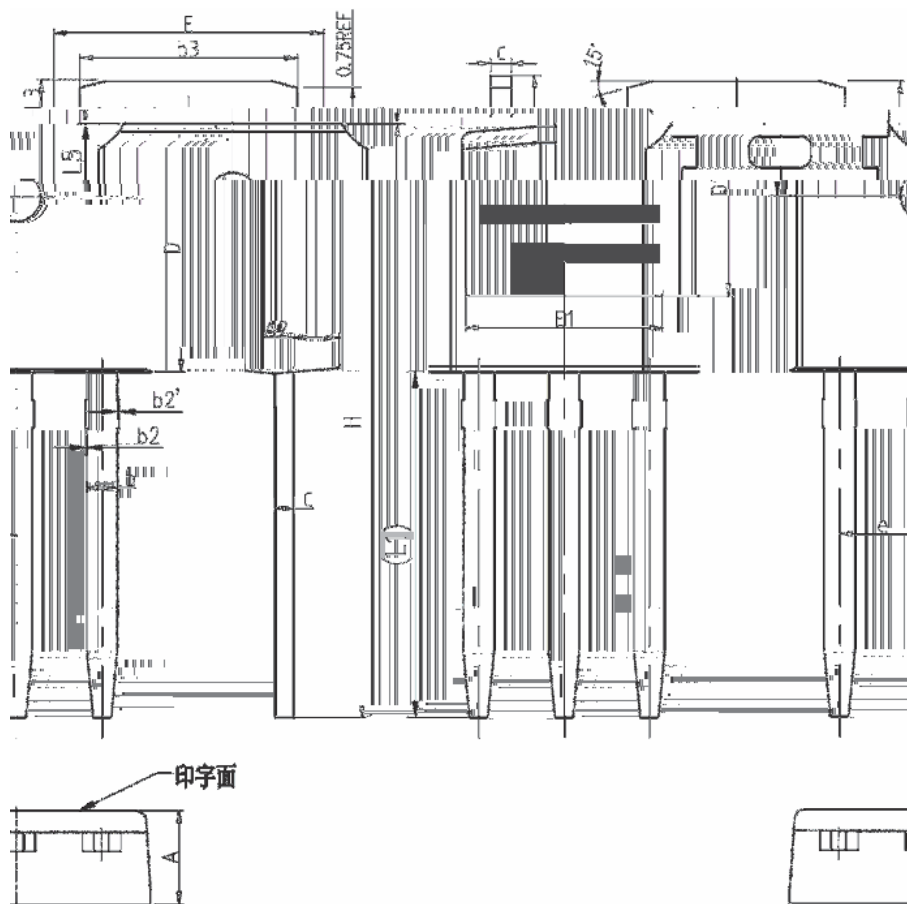
TO-252-2L

COMMON DIMENSIONS

SYMBOL	mm		
	MIN	NOM	MAX
A	2.20	2.30	2.40
A1	0.00	-	0.20
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.50
c	0.43	0.53	0.63
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.80
E1	4.63	-	-
e	2.286BSC		
H	9.40	10.10	10.50
L	1.38	1.50	1.75
L1	2.90REF		
L2	0.51BSC		
L3	0.88	-	1.28
L4	-	-	1.00
L5	1.65	1.80	1.95
	0°	-	8°

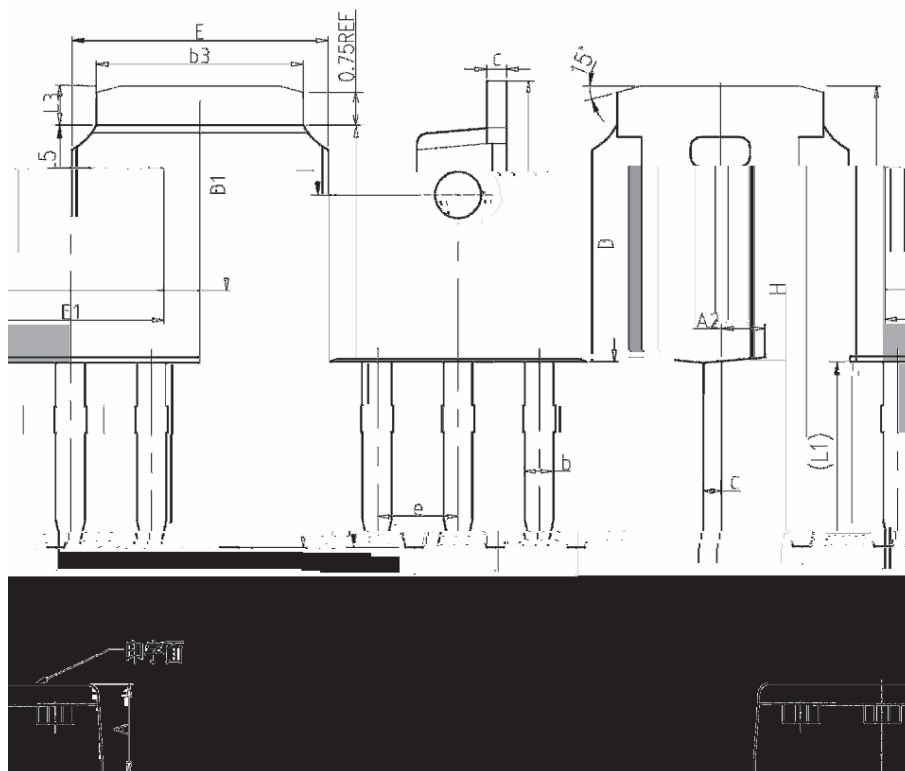


TO-251-3L



COMMON DIMENSIONS

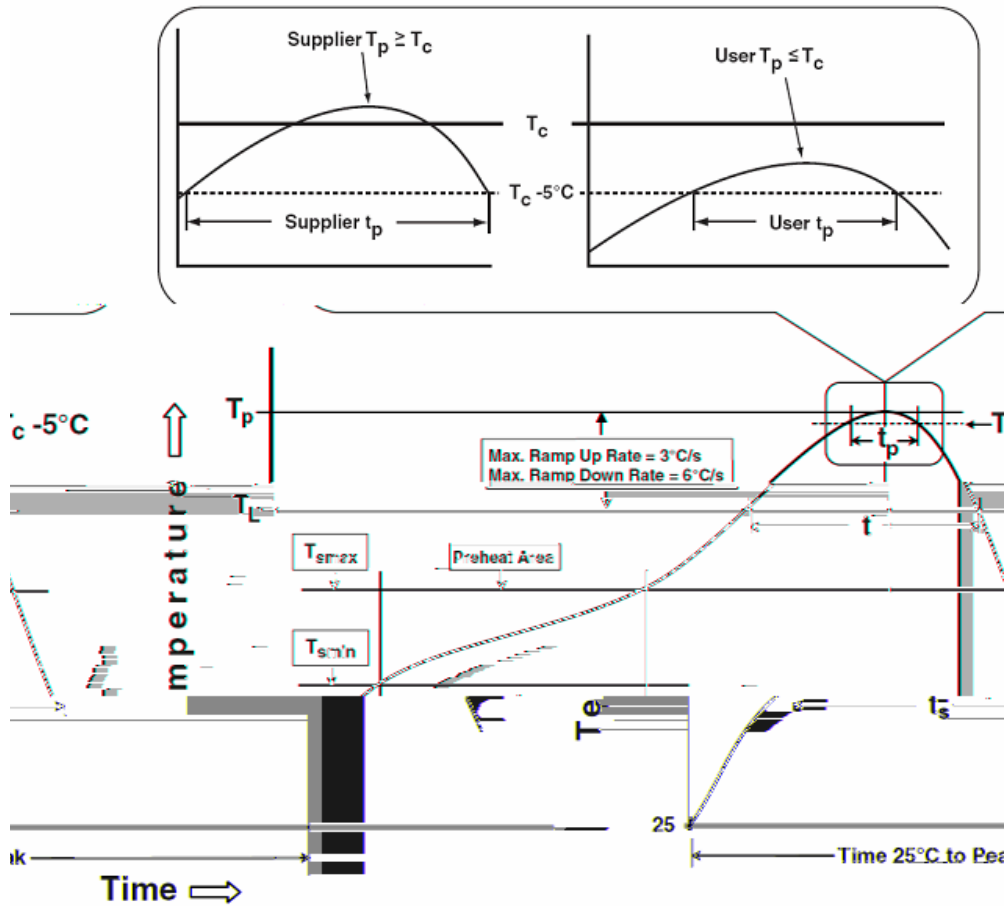
SYMBOL	mm		
	MIN	NOM	MAX
A	2.20	2.30	2.40
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b2	0.00	0.04	0.10
b2'	0.00	0.04	0.10
b3	5.20	5.33	5.50
c	0.43	0.53	0.63
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.80
E1	4.63	-	-
e	2.286BSC		
H	16.22	16.52	16.82
L1	9.15	9.40	9.65
L3	0.88	1.02	1.28
L5	1.65	1.80	1.95



COMMON DIMENSIONS

SYMBOL	mm		
	MIN	NOM	MAX
A	2.20	2.30	2.40
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.50
c	0.43	0.53	0.63
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.80
E1	4.63	-	-
e	2.286BSC		
H	10.00	11.22	11.44
L1	3.90	4.10	4.30
L3	0.88	1.02	1.28
L5	1.65	1.80	1.95

Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.

*Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum.

** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.

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Table 1. SnPb Eutectic Process – Classification Temperatures (Tc)

Package Thickness	Volume mm <350	Volume mm 350
2.5 mm	235 °C	220 °C
2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (Tc)

Package Thickness	Volume mm <350	Volume mm 350-2000	Volume mm 2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description